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Abstract of the disclosure

A ferroelectric random access memory (FeRAM) device,
includes: a plurality of memory cells arranged in an $M \times J$ matrix,
5 wherein M is a positive integer more than three and J is a positive
integer; a number of reference cells connected to each column of
the memory cells; and a cell selection means for selecting a memory
cell in response to address signals from an external circuit and
selecting a reference cell corresponding to the selected memory
10 cell.

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